Claims

1. A semiconductor construction, comprising:
a copper-containing material supported by a silicon-containing base,
a stack over the copper-containing material, the stack comprising a first insulative material over an insulative copper barrier material;
a conductive plug within the stack and directly against the copper-containing material;
an insulative spacer within the stack; the insulative spacer being over and directly against an outer portion of an upper surface of the conductive plug and not directly above an inner portion of the upper surface;
a conductive material over and directly against the inner portion of the upper surface of the conductive plug; the conductive material being directly against an inner lateral surface of the spacer; and
wherein the conductive plug comprises titanium nitride directly against the copper-containing material, and comprises tungsten directly against the titanium nitride.

2. The semiconductor construction of claim 1 wherein the insulative spacer comprises silicon dioxide.

3. The semiconductor construction of claim 1 wherein the insulative spacer comprises silicon nitride.

4. The semiconductor construction of claim 1 wherein the conductive material comprises metal.

5. A semiconductor construction, comprising:
a stack over a first conductive material, the stack comprising a second insulative material over a first insulative material;
the first and second insulative materials being compositionally different from one another;
a conductive plug within the stack and on the first conductive material, the conductive plug having a lateral sidewall directly against both the first and second insulative materials;
an insulative spacer over and directly against an outer portion of an upper surface of the conductive plug and not directly above an inner portion of the upper surface, the insulative spacer having an outer lateral surface directly against the second insulative material of the stack and not directly against the first insulative material of the stack;
a second conductive material over and directly against the inner portion of the upper surface of the conductive plug; the second conductive material being directly against an inner lateral

surface of the spacer; the second conductive material extending along an upper surface of the stack and forming a lower part of a conductive line; and
a third conductive material directly over and along the second conductive material and forming an upper part of the conductive line, the second and third conductive materials being compositionally different from one another.

6. The semiconductor construction of claim 5 wherein the first conductive material is a copper-containing material, and wherein the first insulative material of the stack is a copper barrier material.

7. The semiconductor construction of claim 5 wherein the conductive plug comprises only a single conductive material.

8. The semiconductor construction of claim 5 wherein the conductive plug comprises two or more conductive materials.

9. The semiconductor construction of claim 5 wherein the conductive plug comprises one or both of tungsten and titanium.

10. The semiconductor construction of claim 5 wherein the conductive plug comprises one or more of metal nitride, metal silicide and metal carbide.

11. The semiconductor construction of claim 5 wherein the conductive plug comprises conductively-doped semiconductor material.

12. A method of forming a conductive contact, comprising:
forming an opening through an insulative material to a conductive structure; forming a conductive plug within a bottom region of the opening and directly against the conductive structure;
forming a spacer to line a lateral periphery of an upper region of the opening; the spacer being over and directly against an outer portion of an upper surface of the conductive plug and leaving an inner portion of the upper surface exposed;
forming a conductive material within the lined upper region of the opening and directly against the inner portion of the upper surface of the conductive plug;
forming a conductive line which extends across the insulative material and which is electrically coupled with the conductive structure through the conductive material within the opening; and

wherein the conductive plug comprises titanium nitride directly against copper of the conductive structure, and comprises tungsten directly against the titanium nitride.

13. The method of claim 12 wherein the conductive material comprises metal.

14. The method of claim 12 wherein the conductive line is a bitline or a wordline, and is incorporated into a memory array.

15. The method of claim 14 wherein the memory array is an RRAM array.

16. A method of forming a conductive contact, comprising:
forming an opening through an insulative material to a metal-containing conductive structure;
forming a metal-containing conductive plug within a bottom region of the opening;
forming a spacer along a lateral periphery of an upper region of the opening to narrow the upper region of the opening; the spacer being over an outer portion of an upper surface of the metal-containing conductive plug and leaving an inner portion of the upper surface exposed;
forming a conductive material over the insulative material and within the narrowed upper region of the opening; the conductive material being directly against the inner portion of the upper surface of the metal-containing conductive plug; and
patterning the conductive material into a conductive line that extends across the insulative material and across a region of the conductive material within the opening.

17. The method of claim 16 wherein the narrowed upper region of the opening comprises a first width, and wherein the conductive line has a second width across the opening, with the second width being larger than the first width.

18. The method of claim 16 wherein the conductive line is a bitline or a wordline, and is incorporated into a memory array; and wherein the memory array is an RRAM array.